

WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:
a die pad;
a plurality of semiconductor chips stacked on one surface of the die pad;
a lead extending toward the die pad;
a first wire that is bonded to a first pad of a first semiconductor chip among the plurality of semiconductor chips and to a second pad of a second semiconductor chip among the plurality of semiconductor chips;
a second wire that is bonded to the lead and to one of the first pad and the second pad; and
a sealing material that seals the plurality of semiconductor chips.
2. The semiconductor device according to claim 1, the second semiconductor chip being mounted on the first semiconductor chip, and the second wire being bonded to the lead and to the second pad.
3. The semiconductor device according to claim 2, the second wire being lead out to pass above the first wire.
4. The semiconductor device according to claim 2, the second wire being lead out to traverse the first wire.
5. The semiconductor device according to claim 2, the second wire being overlapped with and bonded to the first wire on the second pad.
6. The semiconductor device according to claim 5, the second wire including a ball formed on a tip thereof, and the ball being press-bonded to the first wire.
7. The semiconductor device according to claim 2, the second wire being bonded to the second pad that is bonded to the first wire, while avoiding a bonded section of the first wire.
8. The semiconductor device according to claim 2,
the second semiconductor chip including a plurality of the second pads,
the plurality of the second pads including a group of pads that are electrically connected to one another by a wiring,
the first wire being bonded to one of the group of pads, and
the second wire being bonded to another of the group of pads.

9. The semiconductor device according to claim 2,
the second pad being provided with a bump, and
the first wire and the second wire being bonded to the second pad through the bump.
10. The semiconductor device according to claim 1, the second semiconductor chip being mounted on the first semiconductor chip, and the second wire being bonded to the lead and to the first pad.
11. The semiconductor device according to claim 2, the first semiconductor chip being a memory, and the second semiconductor chip being a microprocessor.
12. A circuit substrate, comprising:
the semiconductor device according to claim 1.
13. An electronic device, comprising:
the semiconductor device according to claim 1.
14. A method for manufacturing a semiconductor device, comprising:
 - (a) stacking a plurality of semiconductor chips on one surface of a die pad;
 - (b) bonding a first wire to a first pad of a first semiconductor chip among the plurality of semiconductor chips and to a second pad of a second semiconductor chip among the plurality of semiconductor chips;
 - (c) bonding a second wire to a lead that extends toward the die pad and to one of the first pad and the second pad; and
 - (d) sealing the plurality of semiconductor chips.
15. The method for manufacturing a semiconductor device according to claim 14,
step (a) including mounting the second semiconductor chip on the first semiconductor chip, and
step (c) including bonding the second wire to the lead and the second pad.
16. The method for manufacturing a semiconductor device according to claim 15,
step (c) including leading the second wire out to pass over the first wire.
17. The method for manufacturing a semiconductor device according to claim 15,
step (c) including leading the second wire out to traverse the first wire.
18. The method for manufacturing a semiconductor device according to claim 15,
step (c) including providing the second wire so that it is overlapped with and bonded to the first wire on the second pad.

19. The method for manufacturing a semiconductor device according to claim 18, step (c) including forming a ball on a tip portion of the second wire, and press-bonding the ball to the first wire.
20. The method for manufacturing a semiconductor device according to claim 18, steps (b) and (c) including bonding the first wire and the second wire to the second pad without forming balls.
21. The method for manufacturing a semiconductor device according to claim 15, step (c) including bonding the second wire to the second pad that is bonded to the first wire, while avoiding a bonded section of the first wire.
22. The method for manufacturing a semiconductor device according to claim 15, the second semiconductor chip including a plurality of the second pads, the plurality of the second pads including a group of pads that are electrically connected to one another by a wiring, step (b) including bonding the first wire to one of the group of pads, and step (c) including bonding the second wire to another of the group of pads.
23. The method for manufacturing a semiconductor device according to claim 15, steps (b) and (c) including:
providing the second pad with a bump, and
bonding the first wire and the second wire to the second pad through the bump.